L	Hits	Search Text	DB	Time stamp
Number				
1	1609482	memory or storage	USPAT;	2003/04/05
_		-	US-PGPUB;	13:17
			EPO; JPO	1
2	87775	(memory or storage) and (nonvolatile or	USPAT;	2003/04/05
4	0,,,0	non-volatile or floating adj gate)	US-PGPUB;	13:18
		non voluciae of leaves, s y	EPO; JPO	İ
	23	((memory or storage) and (nonvolatile or	USPAT;	2003/04/05
3	23	non-volatile or floating adj gate)) and	US-PGPUB;	13:22
		(voltage or potential or level) with cell	EPO; JPO	
		(Voltage of potential of fever, with our	1210, 010	
		with (current or voltage or time or		
1		frequency) with (sinusoidal or]
		rectangular or trapezoidal)	1	

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L	Hits	Search Text	DB	Time stamp
Number				
1	1609482	memory or storage	USPAT;	2003/04/04
			US-PGPUB;	10:27
	<u> </u>		EPO; JPO	
2	1627	(memory or storage) and set with sens\$5	USPAT;	2003/04/04
		with read\$5 with memory	US-PGPUB;	10:29
	į		EPO; JPO	
3	1265	((memory or storage) and set with sens\$5	USPAT;	2003/04/04
		with read\$5 with memory) and (parameter	US-PGPUB;	10:30
		or current or voltage or time or	EPO; JPO	1
		frequency) with read\$5		
4	319	(((memory or storage) and set with sens\$5	USPAT;	2003/04/04
		with read\$5 with memory) and (parameter	US-PGPUB;	10:33
		or current or voltage or time or	EPO; JPO	•
		frequency) with read\$5) and floating adj		
		gate		1
5	74	((((memory or storage) and set with	USPAT;	2003/04/04
		sens\$5 with read\$5 with memory) and	US-PGPUB;	10:42
		(parameter or current or voltage or time	EPO; JPO	
		or frequency) with read\$5) and floating		
		adj gate) and noise		
6	17	(((((memory or storage) and set with	USPAT;	2003/04/04
		sens\$5 with read\$5 with memory) and	US-PGPUB;	10:43
		(parameter or current or voltage or time	EPO; JPO	
		or frequency) with read\$5) and floating		
		adj gate) and noise) and read\$5 with		
		noise with (reduc\$3 or decreas\$3)		

L	Hits	Search Text	DB	Time stamp
Number 1	1609482	memory or storage	USPAT; US-PGPUB;	2003/04/04 10:54
2	87775	(memory or storage) and (nonvolatile or non-volatile or floating adj gate)	EPO; JPO USPAT; US-PGPUB;	2003/04/04
3	0	((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and appl\$5 with set with voltage with	EPO; JPO USPAT; US-PGPUB; EPO; JPO	2003/04/04
4	14979	episodic adj stimulus ((memory or storage) and (nonvolatile or	USPAT; US-PGPUB;	2003/04/04 11:32
5	49	<pre>(voltage or potential or level) with cell (((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and</pre>	EPO; JPO USPAT; US-PGPUB;	2003/04/04
		(voltage or potential or level) with cell) and measur\$5 with (parameter or current or voltage or time or frequency) with noise	EPO; JPO	14
6	5	<pre>((((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with</pre>	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:40 .
		current or voltage or time or frequency) with noise) and (voltage or potential or level) with (parameter or current or voltage or time or frequency) with noise		
7	926	non-volatile or floating adj gate)) and	USPAT; US-PGPUB; EPO; JPO	2003/04/04
8	2515	non-volatile or floating adj gate)) and apply\$5 with set with voltages) aand determin\$5 with conduction with set with	USPAT; US-PGPUB; EPO; JPO	2003/04/04 11:42
9	1	voltages (((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and apply\$5 with set with voltages) and determin\$5 with conduction with set with	USPAT; US-PGPUB; EPO; JPO	2003/04/04
10	380	non-volatile or floating adj gate)) and (voltage or potential or level) with	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:51
11	13	memory with interval (((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:06
13	0	characteristics with cell (((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with current with cell with (vary\$5 or	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:07
		vari\$5) with (voltage or potential or level)	ист.	2003/04/04
12	53	non-volatile or floating adj gate)) and (voltage or potential or level) with memory with interval) and determin\$5 with	USPAT; US-PGPUB; EPO; JPO	12:08
14	24	current with cell ((memory or storage) and (nonvolatile or non-volatile or floating adj gate)) and (voltage or potential or level) with (vary\$5 or vari\$5) with memory with interval	USPAT; US-PGPUB; EPO; JPO	2003/04/04 12:52